To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

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2SK2929

Silicon N Channel MOS FET
High Speed Power Switching

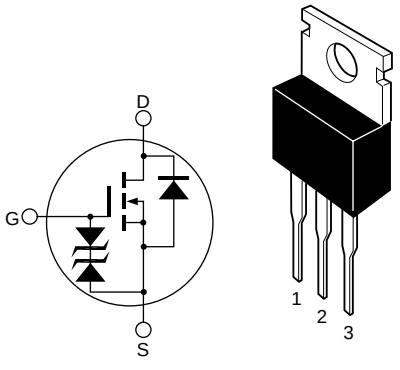
ADE-208-552C (Z)
4th. Edition
Jul. 1998

Features

- Low on-resistance
  R_{DS} =0.026 Ω typ.
- High speed switching
- 4V gate drive device can be driven from 5V source

Outline

TO–220AB



1. Gate
2. Drain(Flange
3. Source

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	25	A
Drain peak current	$I_{D(pulse)}$ Note1	100	A
Body-drain diode reverse drain current	I_{DR}	25	A
Avalanche current	I_{AP} Note3	20	A
Avalanche energy	E_{AR} Note3	34	mJ
Channel dissipation	Pch Note2	50	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Note: 1. PW ≤ 10μs, duty cycle ≤ 1 %
2. Value at Tc = 25°C
3. Value at Tch = 25°C, Rg 50Ω

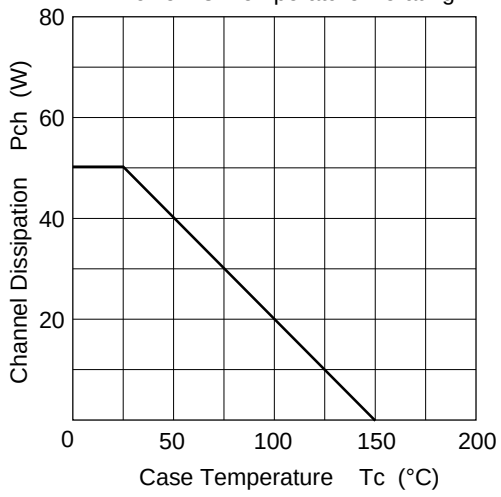
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	I_D = 10mA, V_{GS} = 0
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	I_G = ±100µA, V_{DS} = 0
Gate to source leak current	I_{GSS}	—	—	±10	µA	V_{GS} = ±16V, V_{DS} = 0
Zero gate voltege drain current	I_{DSS}	—	—	10	µA	V_{DS} = 60 V, V_{GS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	1.5	—	2.5	V	I_D = 1mA, V_{DS} = 10V
Static drain to source on state resistance	$R_{DS(on)}$	—	0.026	0.034	Ω	I_D = 15A, V_{GS} = 10V [Note4]
	$R_{DS(on)}$	—	0.045	0.07	Ω	I_D = 15A, V_{GS} = 4V [Note4]
Forward transfer admittance	$\|y_{fs}\|$	11	17	—	S	I_D = 15A, V_{DS} = 10V [Note4]
Input capacitance	Ciss	—	740	—	pF	V_{DS} = 10V
Output capacitance	Coss	—	380	—	pF	V_{GS} = 0
Reverse transfer capacitance	Crss	—	140	—	pF	f = 1MHz
Turn-on delay time	$t_{d(on)}$	—	10	—	ns	I_D = 15A, V_{GS} = 10V
Rise time	t_r	—	160	—	ns	R_L = 2Ω
Turn-off delay time	$t_{d(off)}$	—	100	—	ns	
Fall time	t_f	—	150	—	ns	
Body–drain diode forward voltage	V_{DF}	—	0.95	—	V	I_F = 25A, V_{GS} = 0
Body–drain diode reverse recovery time	t_{rr}	—	40	—	ns	I_F = 25A, V_{GS} = 0 diF/ dt =50A/µs

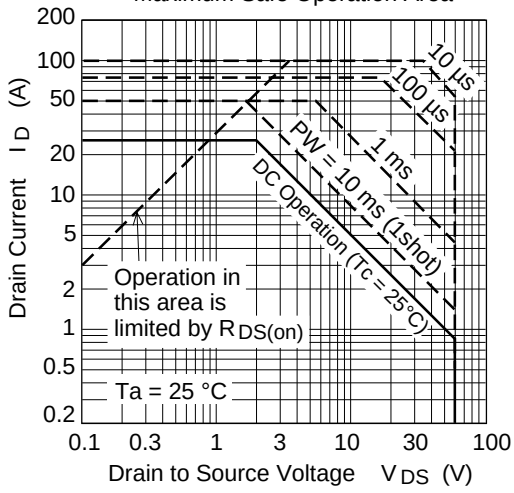
Note: 4. Pulse test

Main Characteristics

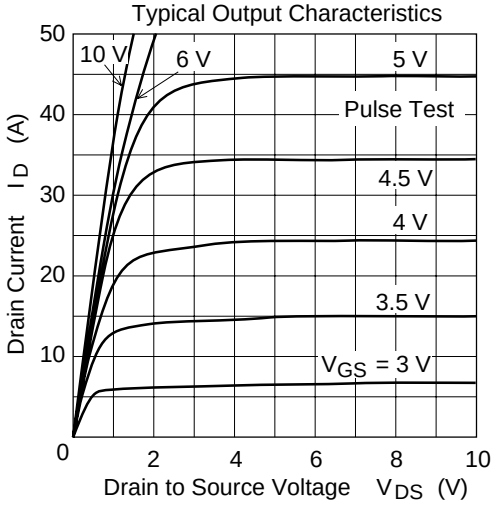
Power vs. Temperature Derating



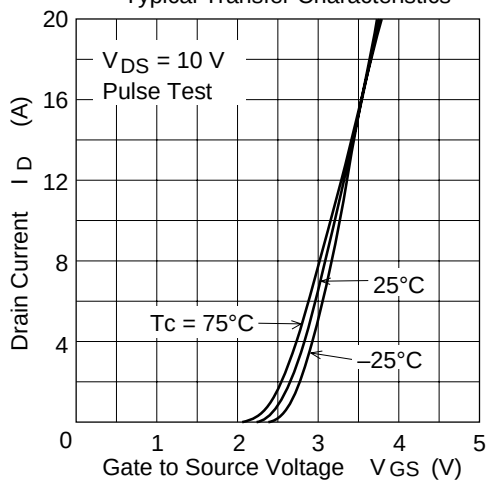
Maximum Safe Operation Area



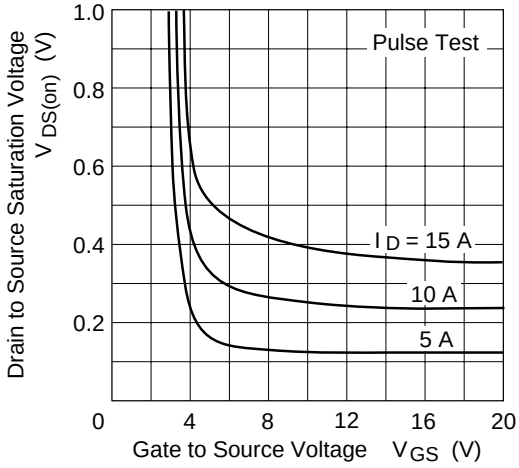
Typical Output Characteristics



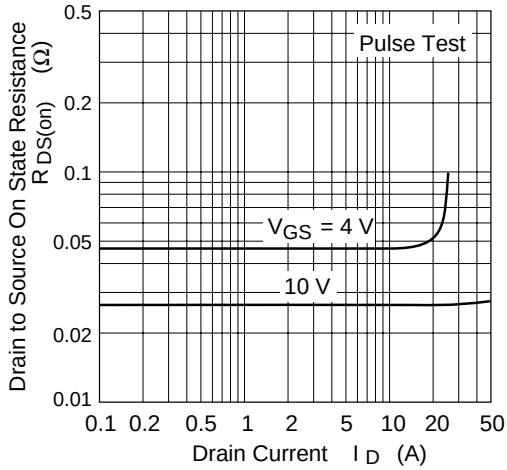
Typical Transfer Characteristics



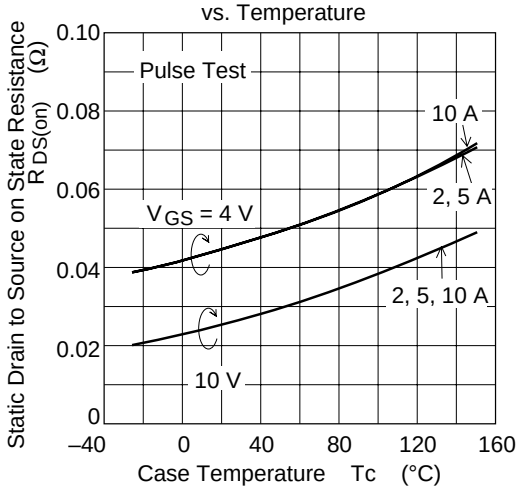
Drain to Source Saturation Voltage vs. Gate to Source Voltage



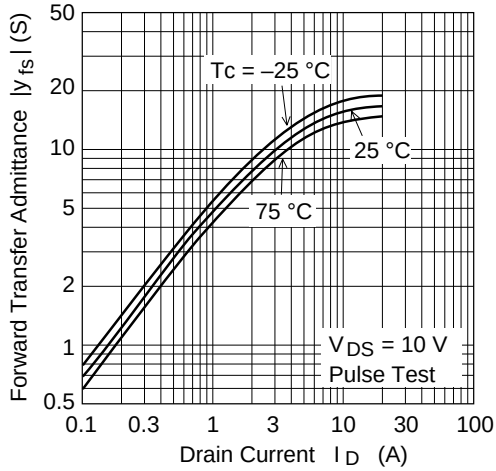
Static Drain to Source on State Resistance vs. Drain Current



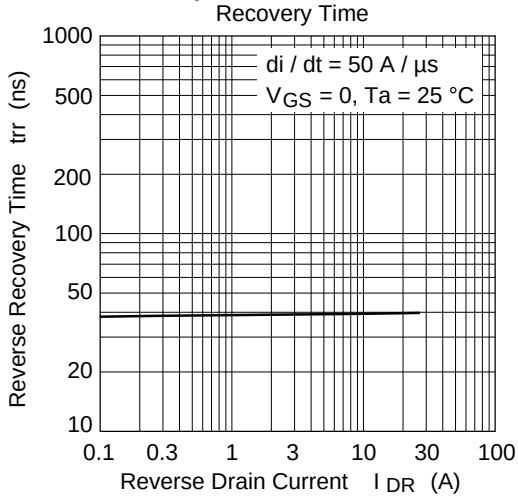
Static Drain to Source on State Resistance vs. Temperature



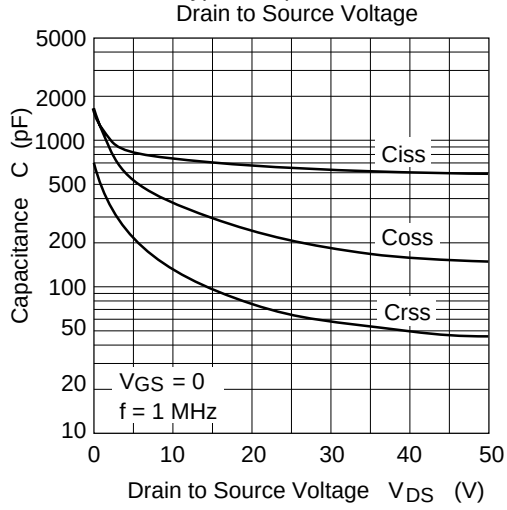
Forward Transfer Admittance vs. Drain Current



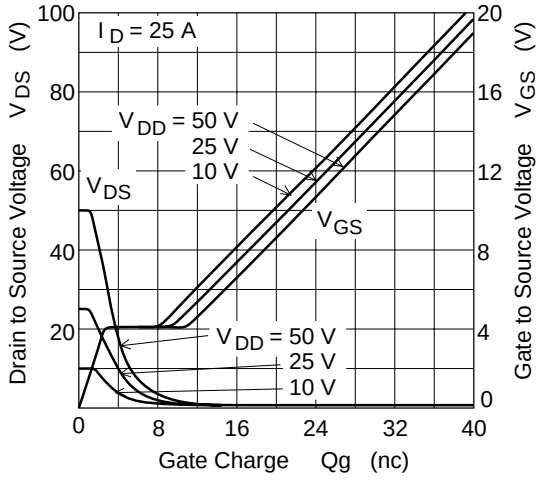
Body–Drain Diode Reverse Recovery Time



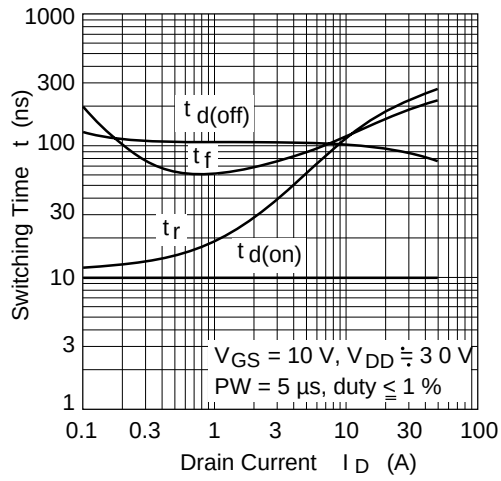
Typical Capacitance vs. Drain to Source Voltage



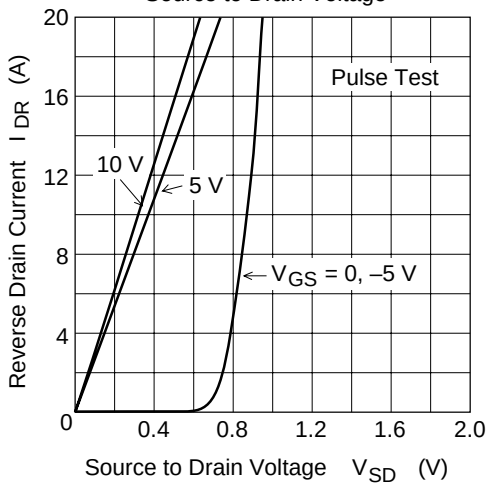
Dynamic Input Characteristics



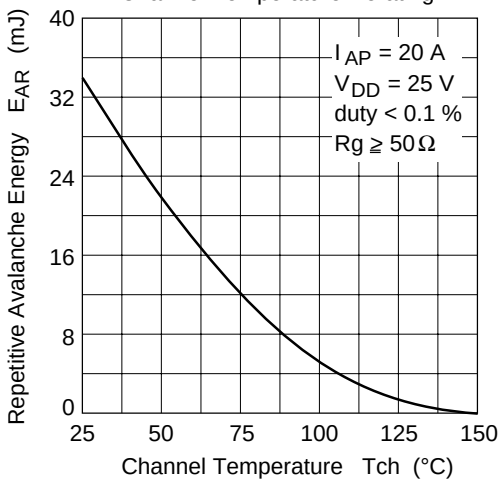
Switching Characteristics



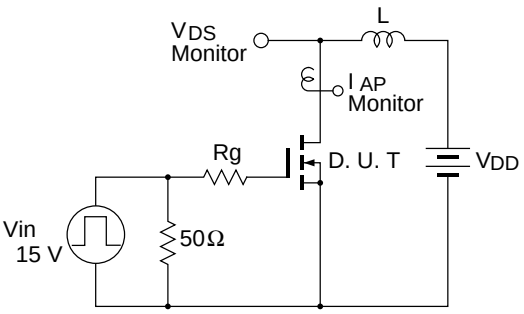
Reverse Drain Current vs.
Source to Drain Voltage



Maximum Avalanche Energy vs.
Channel Temperature Derating

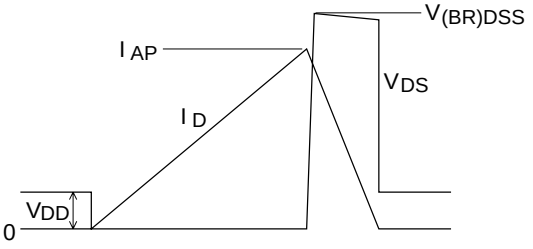


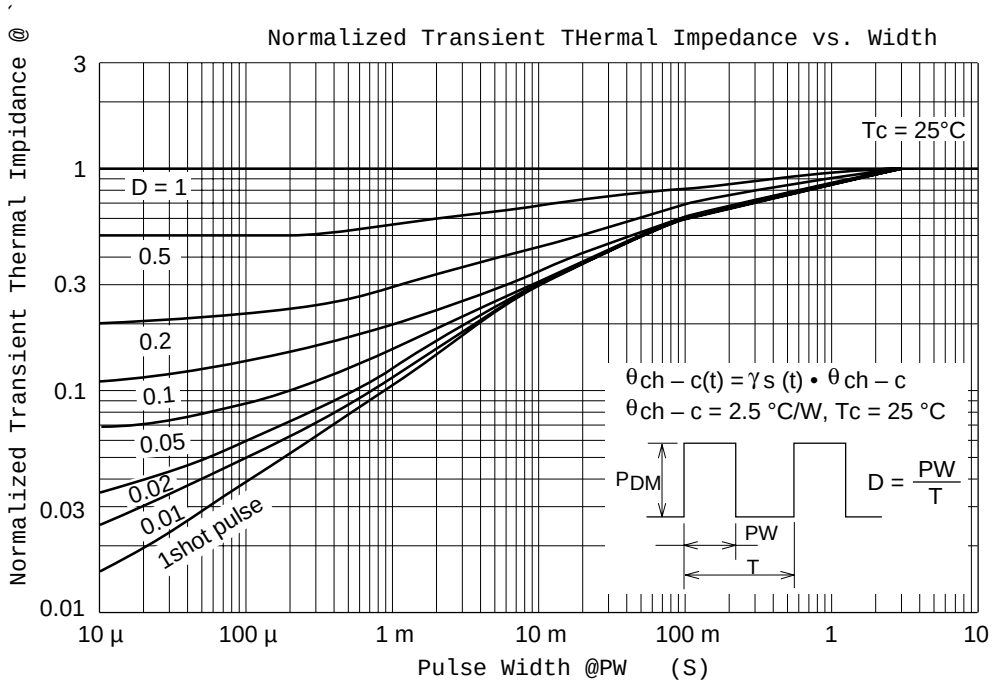
Avalanche Test Circuit



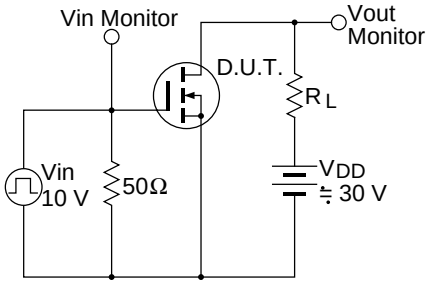
Avalanche Waveform

$$E_{AR} = \frac{1}{2} \bullet L \bullet I_{AP}^{2} \bullet \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$

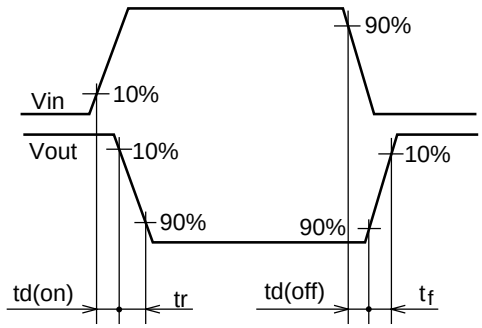




Switching Time Test Circuit



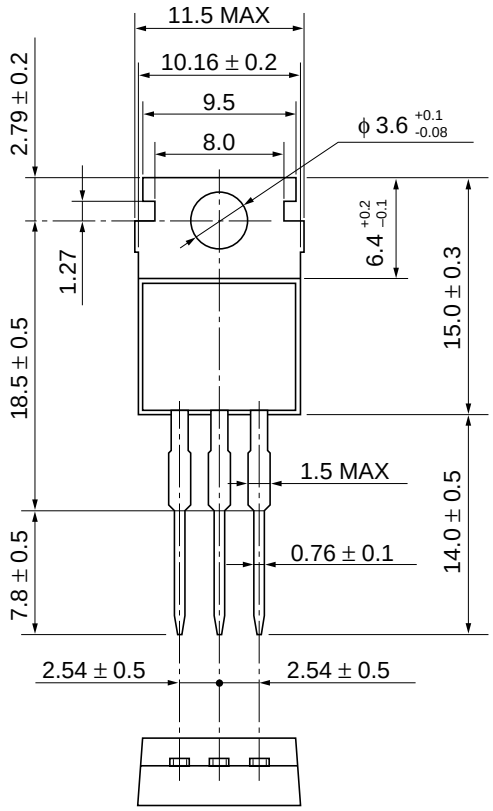
Waveform

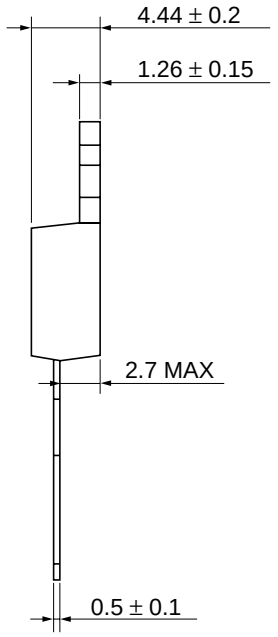


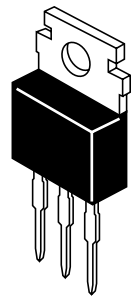
Package Dimensions

As of January, 2001

Unit: mm







Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	1.8 g

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